< Silicon RF Power MOS FET (Discrete) >

RD60HUF1

RoHS Compliance, Silicon MOSFET Power Transistor 520MHz, 60W

DESCRIPTION
RD60HUF1 is a MOS FET type transistor specifically designed for UHF High power amplifiers applications.

FEATURES
High power and High Gain:
- Pout>60W, Gp>7.7dB @Vdd=12.5V, f=520MHz
High Efficiency: 55% typ. on UHF Band

APPLICATION
For output stage of high power amplifiers in UHF Band mobile radio sets.

RoHS COMPLIANT
RD60HUF1-101 is a RoHS compliant product. RoHS compliance is indicated by the letter "G" after the Lot Marking.

ABSOLUTE MAXIMUM RATINGS
(Tc=25°C UNLESS OTHERWISE NOTED)

<table>
<thead>
<tr>
<th>SYMBOL</th>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>RATINGS</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Voss</td>
<td>Drain to source voltage</td>
<td>Vgs=0V</td>
<td>30</td>
<td>V</td>
</tr>
<tr>
<td>Vgss</td>
<td>Gate to source voltage</td>
<td>Vds=0V</td>
<td>+/-20</td>
<td>V</td>
</tr>
<tr>
<td>Pch</td>
<td>Channel dissipation</td>
<td>Tc=25°C</td>
<td>150</td>
<td>W</td>
</tr>
<tr>
<td>Pin</td>
<td>Input power</td>
<td>Zg=Zl=50Ω</td>
<td>20</td>
<td>W</td>
</tr>
<tr>
<td>ID</td>
<td>Drain current</td>
<td>-</td>
<td>20</td>
<td>A</td>
</tr>
<tr>
<td>Tch</td>
<td>Channel temperature</td>
<td>-</td>
<td>175</td>
<td>°C</td>
</tr>
<tr>
<td>Tstg</td>
<td>Storage temperature</td>
<td>-</td>
<td>-40 to +175</td>
<td>°C</td>
</tr>
<tr>
<td>Rth j-c</td>
<td>Thermal resistance</td>
<td>junction to case</td>
<td>1.0</td>
<td>°C/W</td>
</tr>
</tbody>
</table>

Note 1: Above parameters are guaranteed independently.
### ELECTRICAL CHARACTERISTICS  
*(Tc=25°C, UNLESS OTHERWISE NOTED)*

<table>
<thead>
<tr>
<th>SYMBOL</th>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>LIMITS</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>I_DSS</td>
<td>Zerogate voltage drain current</td>
<td>V_DS=17V, V_GS=0V</td>
<td>-</td>
<td>-</td>
</tr>
<tr>
<td>I_GSS</td>
<td>Gate to source leak current</td>
<td>V_GS=10V, V_DS=0V</td>
<td>-</td>
<td>-</td>
</tr>
<tr>
<td>V_TH</td>
<td>Gate threshold voltage</td>
<td>V_DS=12V, I_DS=1mA</td>
<td>1.1</td>
<td>1.45</td>
</tr>
<tr>
<td>P_OUT</td>
<td>Output power</td>
<td>f=520MHz, V_DD=12.5V</td>
<td>60</td>
<td>65</td>
</tr>
<tr>
<td>η_D</td>
<td>Drain efficiency</td>
<td>Pin=10W, I_dq=2.5A</td>
<td>50</td>
<td>55</td>
</tr>
<tr>
<td></td>
<td>Load VSWR tolerance</td>
<td>V_DD=15.2V, P_o=60W(PinControl)</td>
<td>No destroy</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td>f=520MHz, I_dq=2.5A, Z_g=50</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Load VSWR=20:1(All Phase)</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Note: Above parameters, ratings, limits and conditions are subject to change.
< Silicon RF Power MOS FET (Discrete) >

RD60HUF1
RoHS Compliance, Silicon MOSFET Power Transistor 520MHz, 60W

TYPICAL CHARACTERISTICS

CHANNEL DISSIPATION VS. AMBIENT TEMPERATURE

Vgs-Ids CHARACTERISTICS

Vds VS. Ciss CHARACTERISTICS

Vds VS. Crss CHARACTERISTICS

Publication Date: Oct. 2011
TYPICAL CHARACTERISTICS

Pin-Po CHARACTERISTICS

T=+25°C
f=520MHz
Vdd=12.5V
Idq=2.5A

Po (dBm), Gp (dB), Idd (A)

Pin (dBm)

Ta=+25°C
f=520MHz
Vdd=12.5V
Idq=2.5A

Po
ηd (%)
Idd

Pout (W), Idd (A)

Pin (W)

Ta=+25°C
f=520MHz
Vdd=12.5V
Idq=2.5A

Po
ηd
Idd

Vdd-Po CHARACTERISTICS

T=+25°C
f=520MHz
Pin=10W
Idq=2.5A
Zg=ZI=50 ohm

Vdd (V)
Po (W)
Idd (A)

Ta=-25°C
f=520MHz
Vdd=12.5V
Idq=2.5A

Po
ηd
Idd

Vgs-Ids CHARACTERISTICS 2

Tc=-25~+75°C

Vgs (V)
Ids (A)

Vds=10V

Tc=+25°C

Vgs (V)
Ids (A)

Tc=-25~+75°C

Tc=+25°C
TEST CIRCUIT (f=520MHz)

C1: 2200pF 10uf in parallel
C2: 2200pF*2 in parallel
C3: 2200pF, 330μF in parallel
L1: 4Turns, I. D6mm, D1. 6mm P=1 silver plated copper wire
L2: 2Turns, I. D6mm, D1. 6mm P=1 silver plated copper wire
L3: 4Turns, I. D6mm, D1. 6mm P=1 silver plated copper wire

Note: Board material PTFE substrate
microstrip line width=4.2mm/500Ω, εr=2.7, t=1.6mm
Dimensions:mm
INPUT/OUTPUT IMPEDANCE VS. FREQUENCY CHARACTERISTICS

<table>
<thead>
<tr>
<th>f (MHz)</th>
<th>Zin (ohm)</th>
<th>Zout (ohm)</th>
<th>Conditions</th>
</tr>
</thead>
<tbody>
<tr>
<td>300</td>
<td>1.16-j0.06</td>
<td>0.83+j0.14</td>
<td>Po=70W, Vdd=12.5V, Pin=10W</td>
</tr>
<tr>
<td>440</td>
<td>1.18+j0.09</td>
<td>1.20+j0.58</td>
<td>Po=65W, Vdd=12.5V, Pin=10W</td>
</tr>
<tr>
<td>520</td>
<td>1.15+j0.86</td>
<td>1.05+j1.09</td>
<td>Po=60W, Vdd=12.5V, Pin=10W</td>
</tr>
</tbody>
</table>
RD60HUF1  S-PARAMETER DATA (@Vdd=12.5V, Id=500mA)

<table>
<thead>
<tr>
<th>Freq. [MHz]</th>
<th>S11 (mag)</th>
<th>S11 (ang)</th>
<th>S21 (mag)</th>
<th>S21 (ang)</th>
<th>S12 (mag)</th>
<th>S12 (ang)</th>
<th>S22 (mag)</th>
<th>S22 (ang)</th>
</tr>
</thead>
<tbody>
<tr>
<td>10</td>
<td>0.909</td>
<td>-156.8</td>
<td>30.933</td>
<td>98.0</td>
<td>0.012</td>
<td>8.6</td>
<td>0.788</td>
<td>-166.6</td>
</tr>
<tr>
<td>50</td>
<td>0.910</td>
<td>-177.1</td>
<td>6.014</td>
<td>75.6</td>
<td>0.011</td>
<td>-10.8</td>
<td>0.811</td>
<td>-177.2</td>
</tr>
<tr>
<td>100</td>
<td>0.923</td>
<td>178.6</td>
<td>2.796</td>
<td>60.1</td>
<td>0.010</td>
<td>-25.0</td>
<td>0.845</td>
<td>-178.5</td>
</tr>
<tr>
<td>150</td>
<td>0.935</td>
<td>175.5</td>
<td>1.678</td>
<td>46.1</td>
<td>0.008</td>
<td>-32.2</td>
<td>0.869</td>
<td>178.3</td>
</tr>
<tr>
<td>175</td>
<td>0.944</td>
<td>173.9</td>
<td>1.351</td>
<td>40.5</td>
<td>0.008</td>
<td>-39.0</td>
<td>0.877</td>
<td>177.0</td>
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<tr>
<td>200</td>
<td>0.949</td>
<td>172.5</td>
<td>1.109</td>
<td>36.2</td>
<td>0.007</td>
<td>-41.7</td>
<td>0.893</td>
<td>175.6</td>
</tr>
<tr>
<td>250</td>
<td>0.957</td>
<td>169.2</td>
<td>0.804</td>
<td>27.2</td>
<td>0.005</td>
<td>-42.3</td>
<td>0.930</td>
<td>172.3</td>
</tr>
<tr>
<td>300</td>
<td>0.961</td>
<td>166.2</td>
<td>0.583</td>
<td>18.3</td>
<td>0.004</td>
<td>-40.2</td>
<td>0.930</td>
<td>169.2</td>
</tr>
<tr>
<td>350</td>
<td>0.964</td>
<td>163.3</td>
<td>0.450</td>
<td>12.0</td>
<td>0.003</td>
<td>-21.8</td>
<td>0.945</td>
<td>166.0</td>
</tr>
<tr>
<td>400</td>
<td>0.969</td>
<td>159.8</td>
<td>0.368</td>
<td>6.8</td>
<td>0.002</td>
<td>-4.8</td>
<td>0.957</td>
<td>162.4</td>
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<tr>
<td>450</td>
<td>0.974</td>
<td>157.0</td>
<td>0.296</td>
<td>2.3</td>
<td>0.002</td>
<td>38.1</td>
<td>0.956</td>
<td>159.5</td>
</tr>
<tr>
<td>500</td>
<td>0.975</td>
<td>153.8</td>
<td>0.238</td>
<td>-3.0</td>
<td>0.003</td>
<td>38.4</td>
<td>0.962</td>
<td>156.5</td>
</tr>
<tr>
<td>550</td>
<td>0.977</td>
<td>151.0</td>
<td>0.209</td>
<td>-6.1</td>
<td>0.003</td>
<td>49.4</td>
<td>0.965</td>
<td>153.4</td>
</tr>
<tr>
<td>600</td>
<td>0.978</td>
<td>147.8</td>
<td>0.178</td>
<td>-14.1</td>
<td>0.005</td>
<td>53.8</td>
<td>0.963</td>
<td>150.1</td>
</tr>
<tr>
<td>650</td>
<td>0.982</td>
<td>145.1</td>
<td>0.155</td>
<td>-17.5</td>
<td>0.006</td>
<td>54.4</td>
<td>0.971</td>
<td>147.4</td>
</tr>
<tr>
<td>700</td>
<td>0.983</td>
<td>141.9</td>
<td>0.136</td>
<td>-19.6</td>
<td>0.006</td>
<td>50.3</td>
<td>0.973</td>
<td>144.5</td>
</tr>
<tr>
<td>750</td>
<td>0.979</td>
<td>139.5</td>
<td>0.113</td>
<td>-17.5</td>
<td>0.007</td>
<td>51.8</td>
<td>0.972</td>
<td>141.5</td>
</tr>
<tr>
<td>800</td>
<td>0.982</td>
<td>136.7</td>
<td>0.104</td>
<td>-20.2</td>
<td>0.009</td>
<td>56.2</td>
<td>0.980</td>
<td>139.4</td>
</tr>
<tr>
<td>850</td>
<td>0.985</td>
<td>133.7</td>
<td>0.103</td>
<td>-33.3</td>
<td>0.009</td>
<td>49.6</td>
<td>0.978</td>
<td>136.2</td>
</tr>
<tr>
<td>900</td>
<td>0.980</td>
<td>130.9</td>
<td>0.084</td>
<td>-27.4</td>
<td>0.010</td>
<td>46.5</td>
<td>0.975</td>
<td>133.1</td>
</tr>
<tr>
<td>950</td>
<td>0.981</td>
<td>128.0</td>
<td>0.083</td>
<td>-35.1</td>
<td>0.010</td>
<td>47.2</td>
<td>0.983</td>
<td>130.4</td>
</tr>
<tr>
<td>1000</td>
<td>0.981</td>
<td>124.9</td>
<td>0.071</td>
<td>-28.7</td>
<td>0.012</td>
<td>43.8</td>
<td>0.984</td>
<td>128.0</td>
</tr>
</tbody>
</table>
ATTENTION:
1. High Temperature; This product might have a heat generation while operation. Please take notice that have a possibility to receive a burn to touch the operating product directly or touch the product until cold after switch off. At the near the product, do not place the combustible material that have possibilities to arise the fire.
2. Generation of High Frequency Power; This product generate a high frequency power. Please take notice that do not leakage the unnecessary electric wave and use this products without cause damage for human and property per normal operation.
3. Before use; Before use the product, Please design the equipment in consideration of the risk for human and electric wave obstacle for equipment.

PRECAUTIONS FOR THE USE OF MITSUBISHI SILICON RF POWER DEVICES:
1. The specifications of mention are not guarantee values in this data sheet. Please confirm additional details regarding operation of these products from the formal specification sheet. For copies of the formal specification sheets, please contact one of our sales offices.

2. RA series products (RF power amplifier modules) and RD series products (RF power transistors) are designed for consumer mobile communication terminals and were not specifically designed for use in other applications. In particular, while these products are highly reliable for their designed purpose, they are not manufactured under a quality assurance testing protocol that is sufficient to guarantee the level of reliability typically deemed necessary for critical communications elements and in the application, which is base station applications and fixed station applications that operate with long term continuous transmission and a higher on-off frequency during transmitting, please consider the derating, the redundancy system, appropriate setting of the maintain period and others as needed. For the reliability report which is described about predicted operating life time of Mitsubishi Silicon RF Products, please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor.

3. RD series products use MOSFET semiconductor technology. They are sensitive to ESD voltage therefore appropriate ESD precautions are required.

4. In the case of use in below than recommended frequency, there is possibility to occur that the device is deteriorated or destroyed due to the RF-swing exceed the breakdown voltage.

5. In order to maximize reliability of the equipment, it is better to keep the devices temperature low. It is recommended to utilize a sufficient sized heat-sink in conjunction with other cooling methods as needed (fan, etc.) to keep the channel temperature for RD series products lower than 120deg/C (in case of Tchmax=150deg/C), 140deg/C (in case of Tchmax=175deg/C) under standard conditions.

6. Do not use the device at the exceeded the maximum rating condition. In case of plastic molded devices, the exceeded maximum rating condition may cause blowout, smoldering or catch fire of the molding resin due to extreme short current flow between the drain and the source of the device. These results causes in fire or injury.

7. For specific precautions regarding assembly of these products into the equipment, please refer to the supplementary items in the specification sheet.

8. Warranty for the product is void if the products protective cap (lid) is removed or if the product is modified in any way from it’s original form.

9. For additional “Safety first” in your circuit design and notes regarding the materials, please refer the last page of this data sheet.

10. Please refer to the additional precautions in the formal specification sheet.
Keep safety first in your circuit designs!

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